

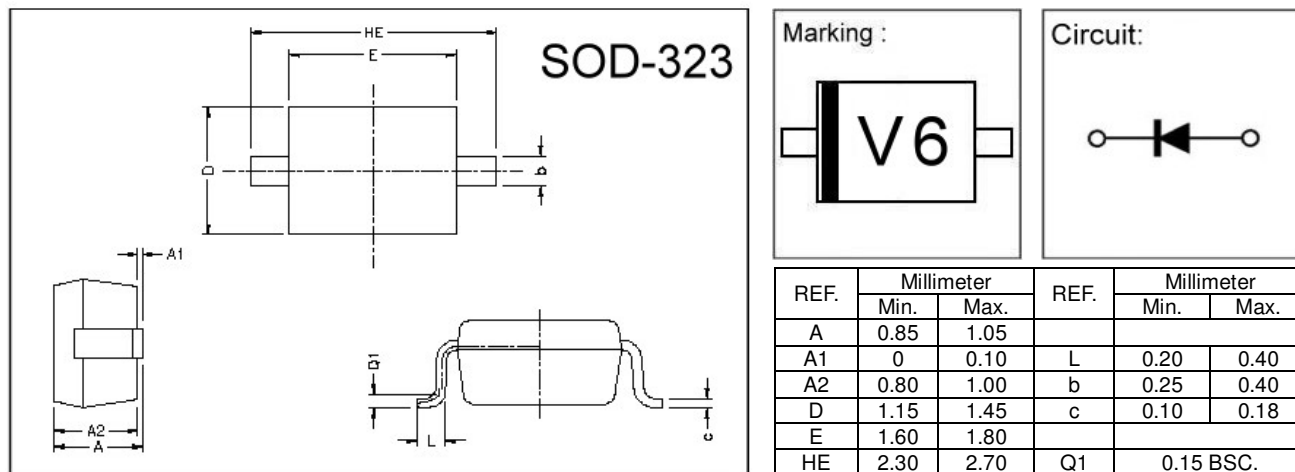
GD421SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.1A

Description

The GD421SD is designed for low power rectification.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	°C
Storage Temperature	Tstg	-40 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40	V
Maximum RMS Voltage	V _{RPS}	28	V
Maximum DC Blocking Voltage	V _{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	1.0	A
Typical Junction Capacitance between Terminal	C _J	6.0	pF
Maximum Average Forward Rectified Current	I _o	0.1	A
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _{(BR)R}	40	-	-	V	I _R =50μA
Forward Voltage	V _{F(1)}	-	-	340	mV	I _F =10mA
	V _{F(2)}	-	-	550	mV	I _F =100mA
Reverse Leakage Current	I _R	-	-	30	μA	V _R =10V

Characteristics Curve

FIG. 1 - FORWARD CHARACTERISTICS

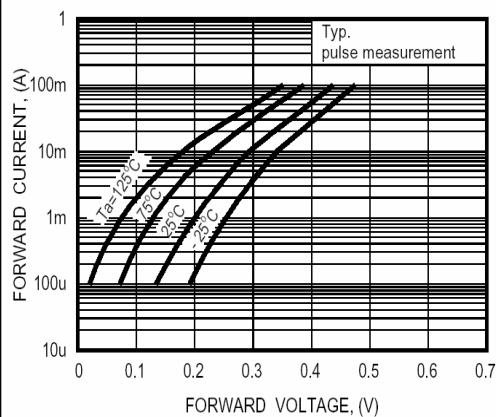


FIG. 2 - REVERSE CHARACTERISTICS

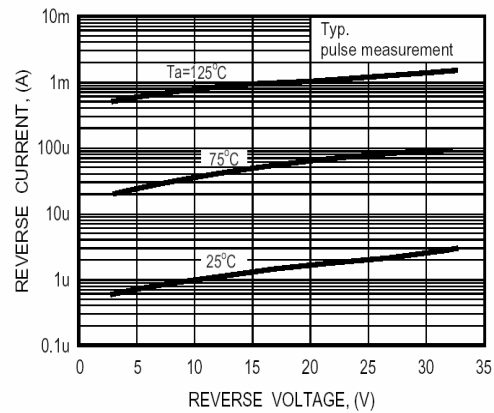


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

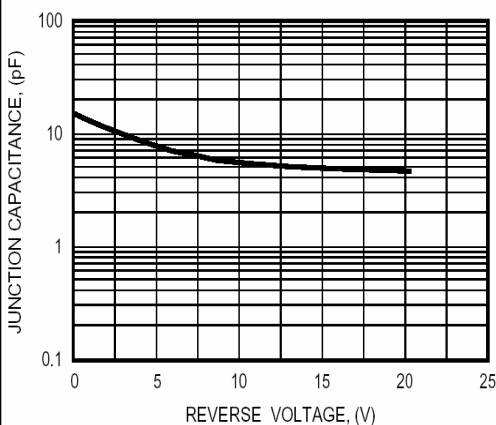
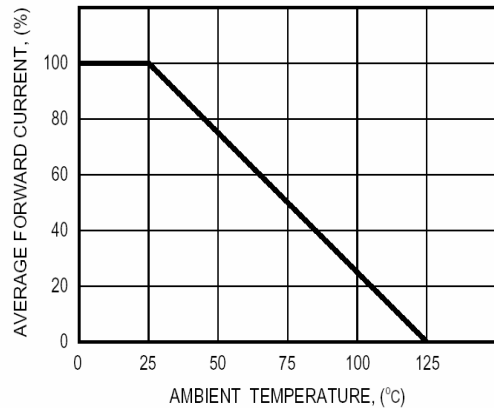


FIG. 4 - TYPICAL FORWARD CURRENT DERRATING CURVE

**Important Notice:**

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165